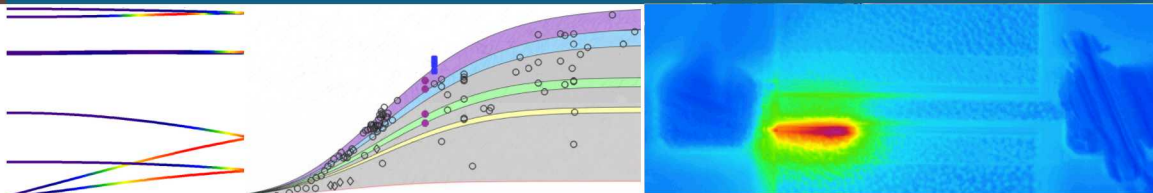
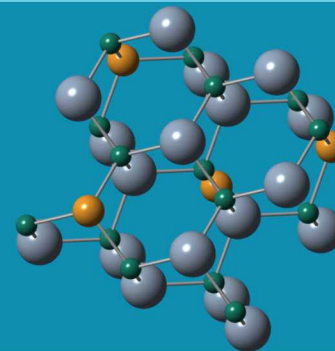


Size Dictated Thermal Conductivity of GaN and AlGaN



Thomas Beechem

Team

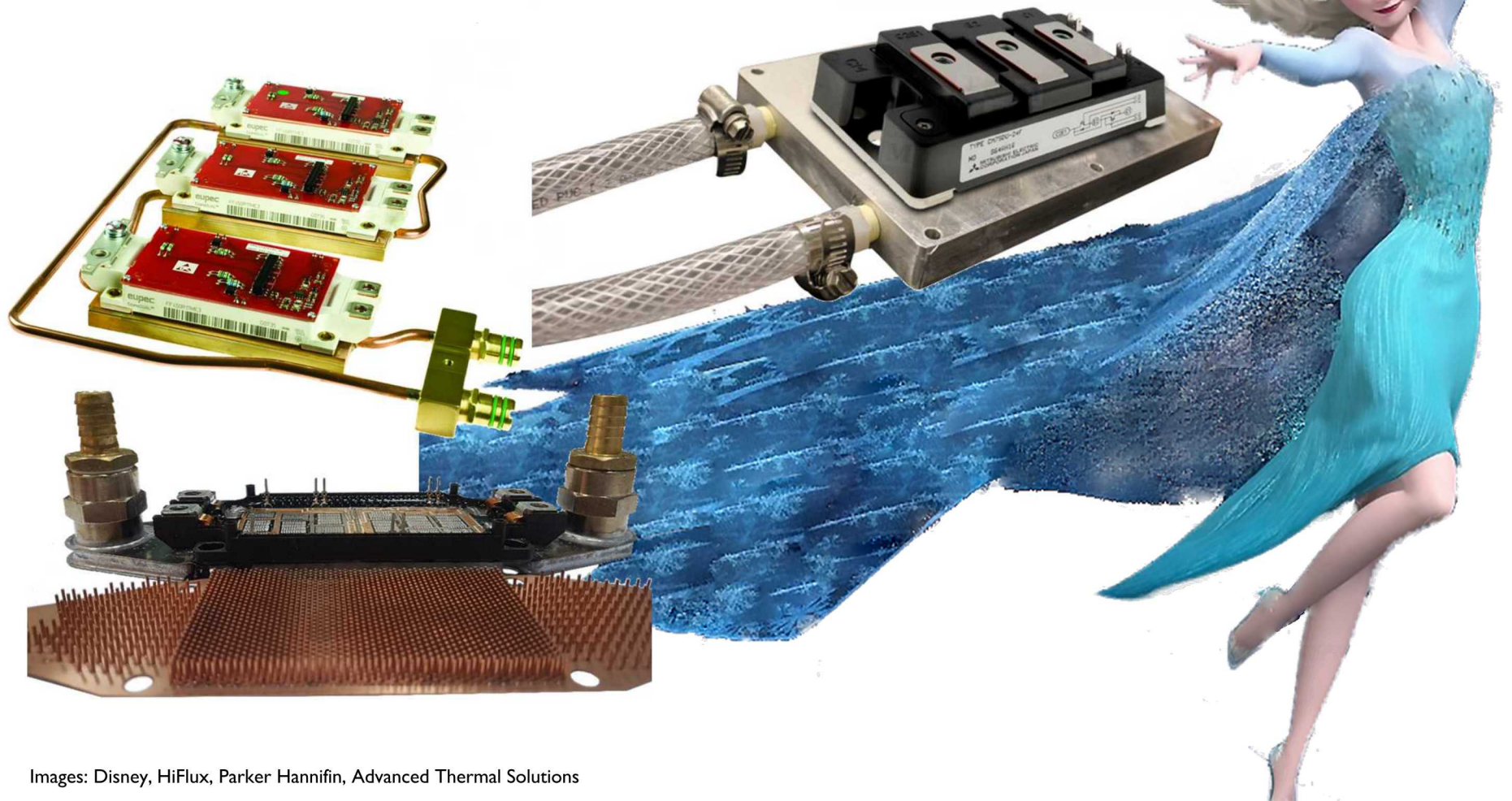
Chris Saltonstall, Hamid Seyf (GT), Asegun Henry (MIT), and Andrew Allerman



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Typical Thermal Management

Frozen Approach ➡ Throw cold at the device



Opportunity: Wide Bandgap Power Devices

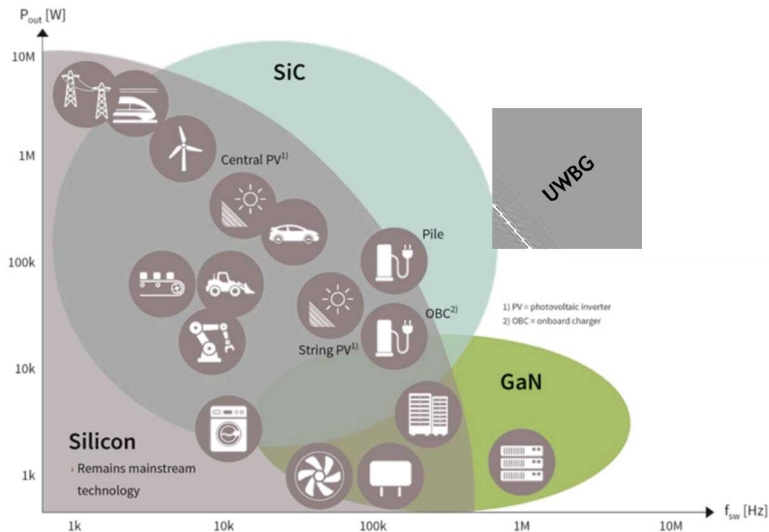


Image: Adapted from Infineon

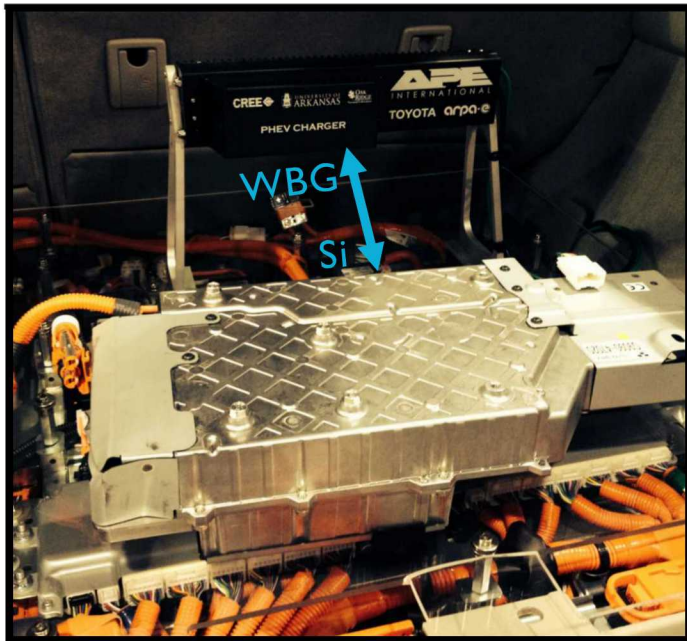
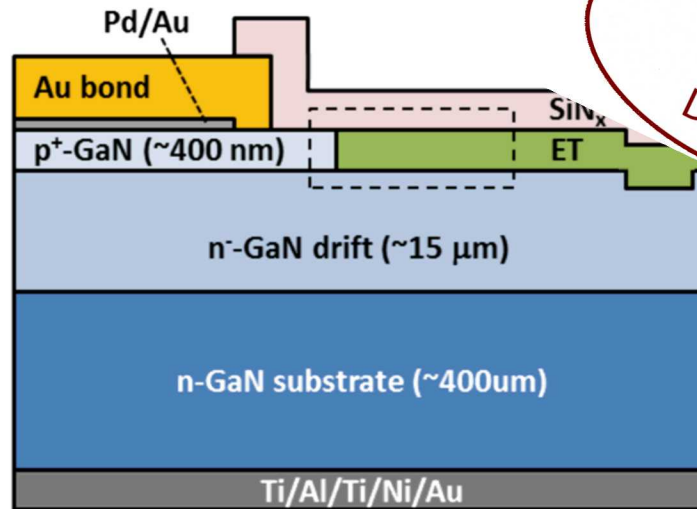


Image: Kiziyalli et al. WBG Semi. Based Power Elec. for Energy Efficiency. ARPA-E Report. 2018.

Thermal design from “growth up”



Vertical Power Diode

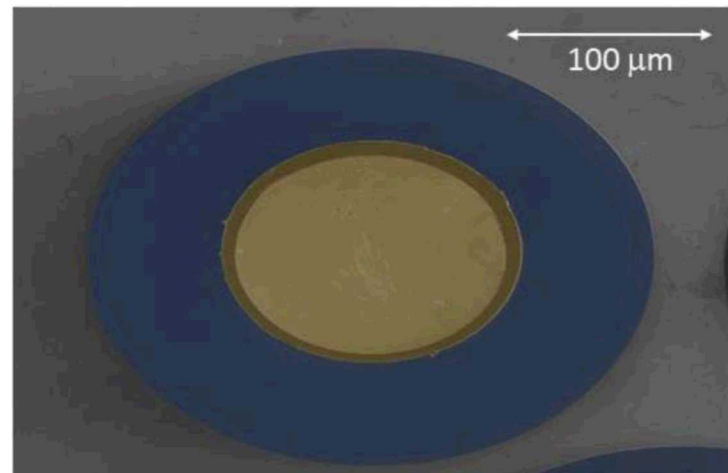


Image: Dickerson et al. IEEE Trans. Elec. Dev. (63) 419. 2016.

Do we know enough to design from “growth up”?

Phonon Gas (PG)
Model
RTA

$$k = \frac{1}{6\pi^2} \sum_s \int_0^{q_{m,s}} \frac{\hbar^2 \omega^2(q)}{k_B T^2} \frac{\exp\left(\frac{\hbar \omega(q)}{k_B T}\right)}{\left[\exp\left(\frac{\hbar \omega(q)}{k_B T}\right) - 1\right]^2} v^2(q) \tau_s(q) q^2 dq$$

Impurities



$$\tau_I^{-1} \propto \omega^{-4}$$

Size Effects



$$\tau_L^{-1} \propto L^{-1}$$

Dislocations

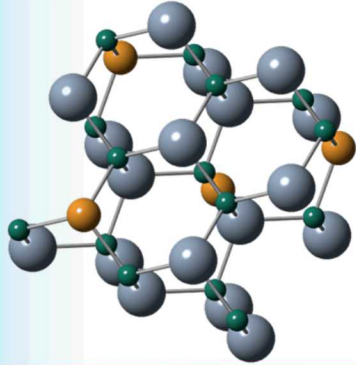


$$\tau_D^{-1} \propto \omega^{-3}$$

Goal: Understand what effects matter when in GaN and AlGaN

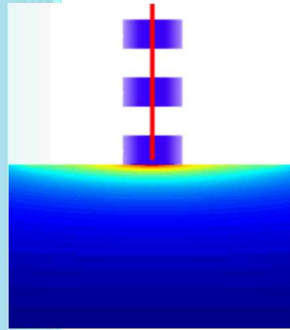
Approach: Make, Measure, Model

Make



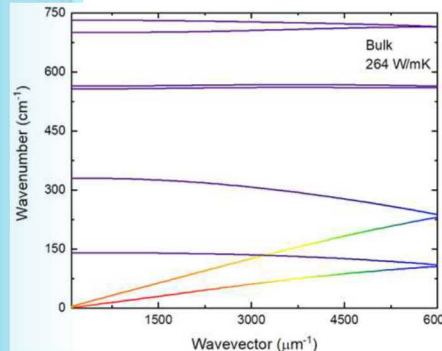
Material: MOCVD GaN/AlGaN
Variables: Doping, Alloying, Thickness

Measure



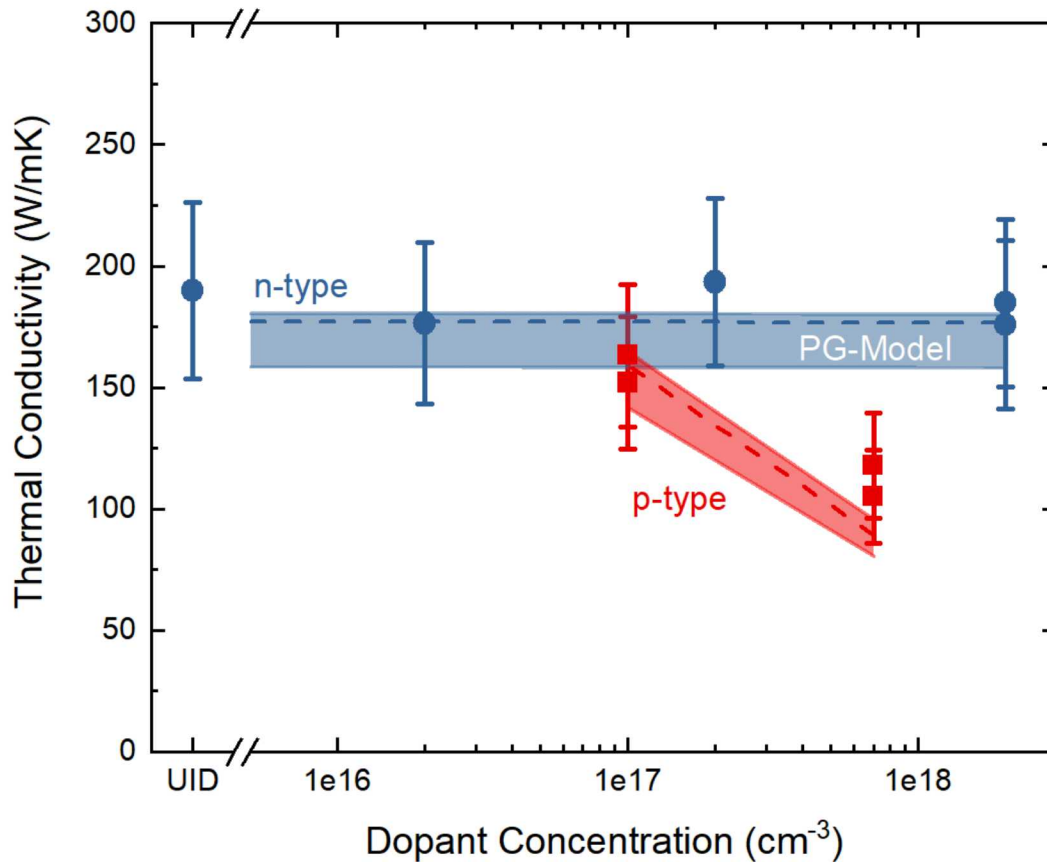
Tool: Time Domain Thermoreflectance

Model



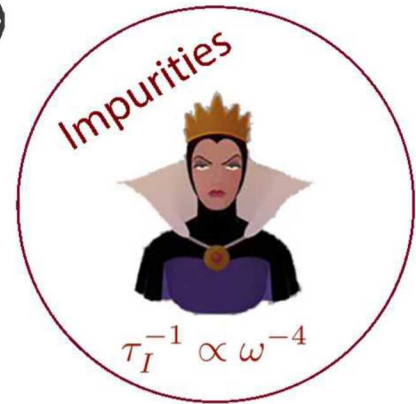
Approach:
Phonon Gas Model
DFT/Lattice Dynamics
Allen-Feldman Theory

Measure: An Unsuspected Insensitivity

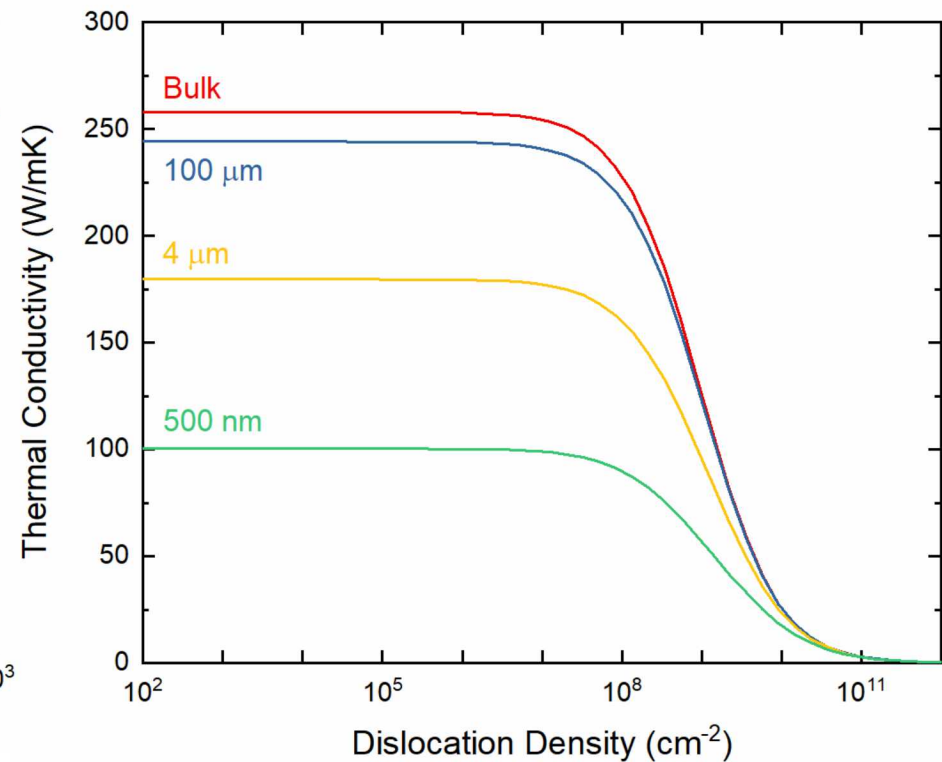
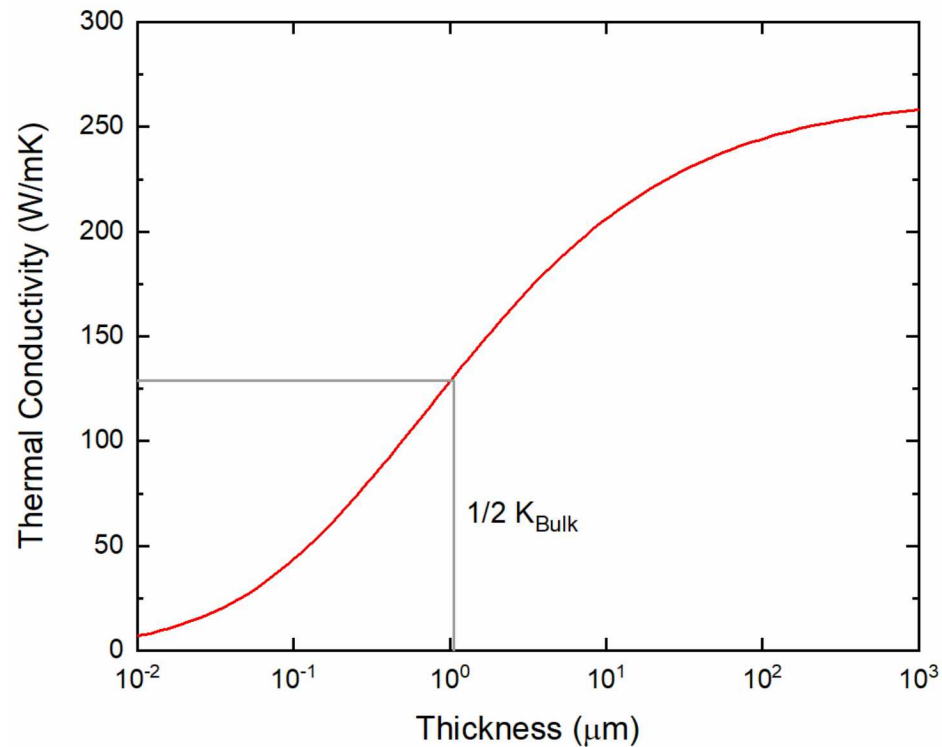


p-type
Sensitive

n-type
Immune?

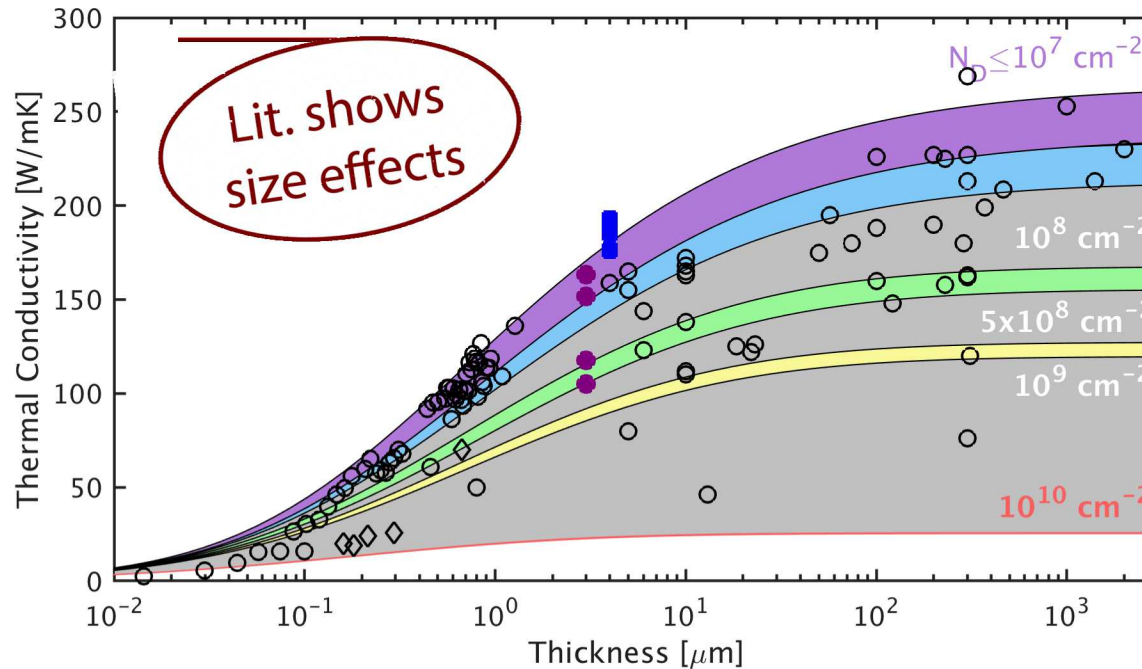


Phonon-Gas Model: Probing the Pain Points

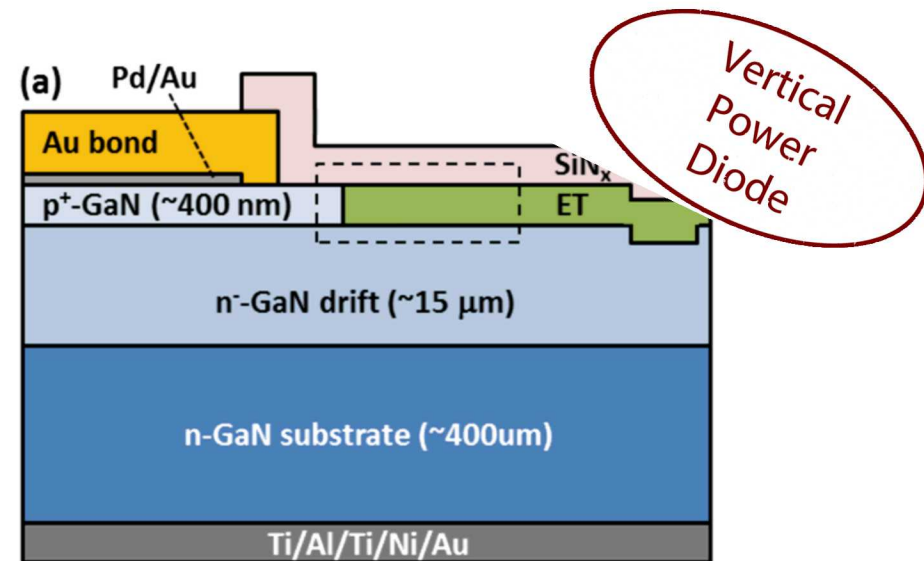


Takeaway: Size dictates thermal conductivity of GaN?

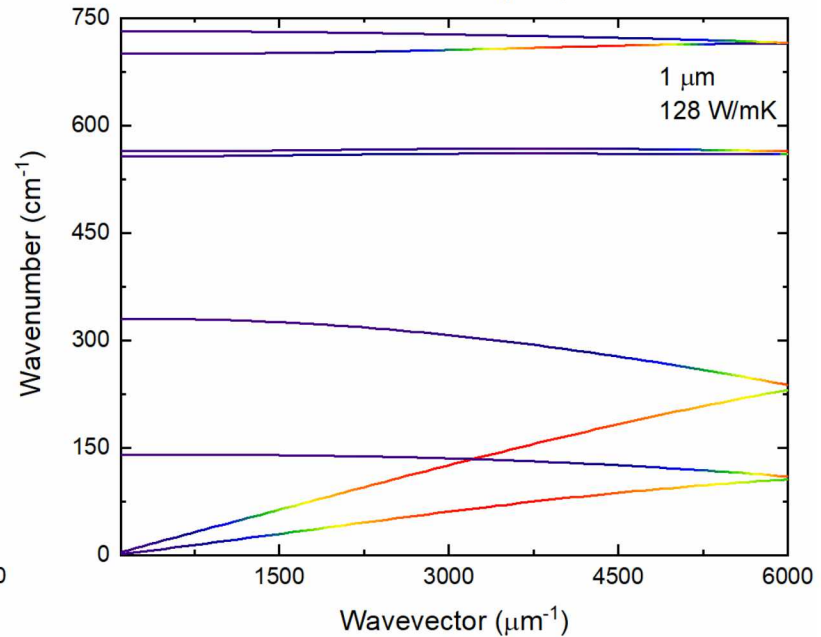
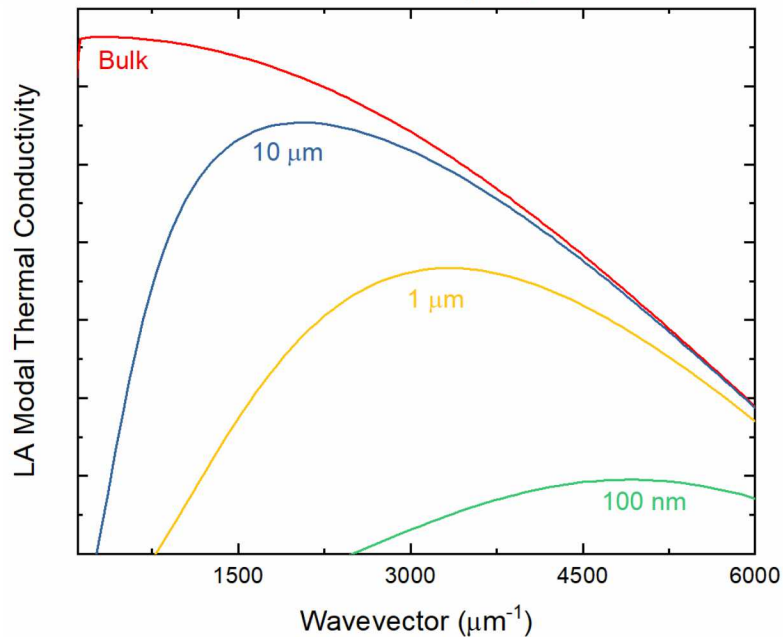
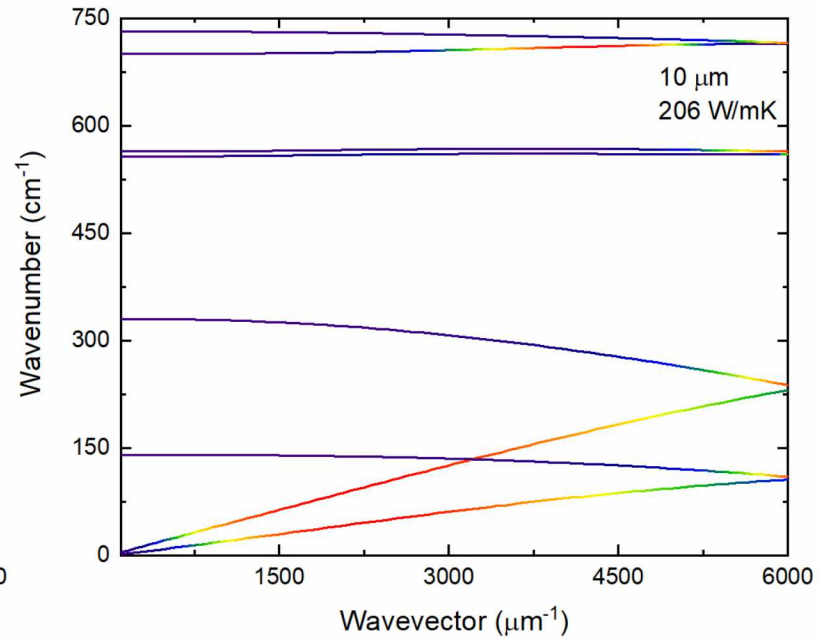
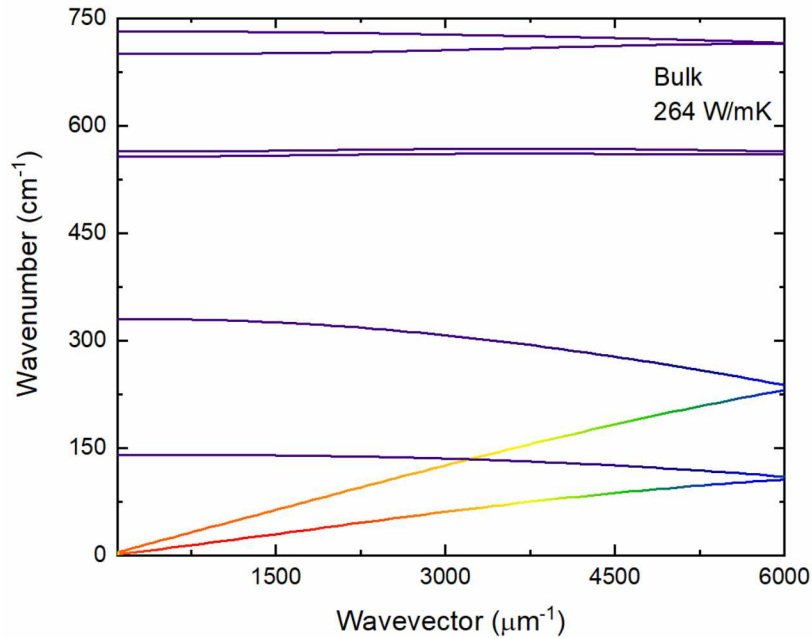
Bottom Line: Implications on Device Design



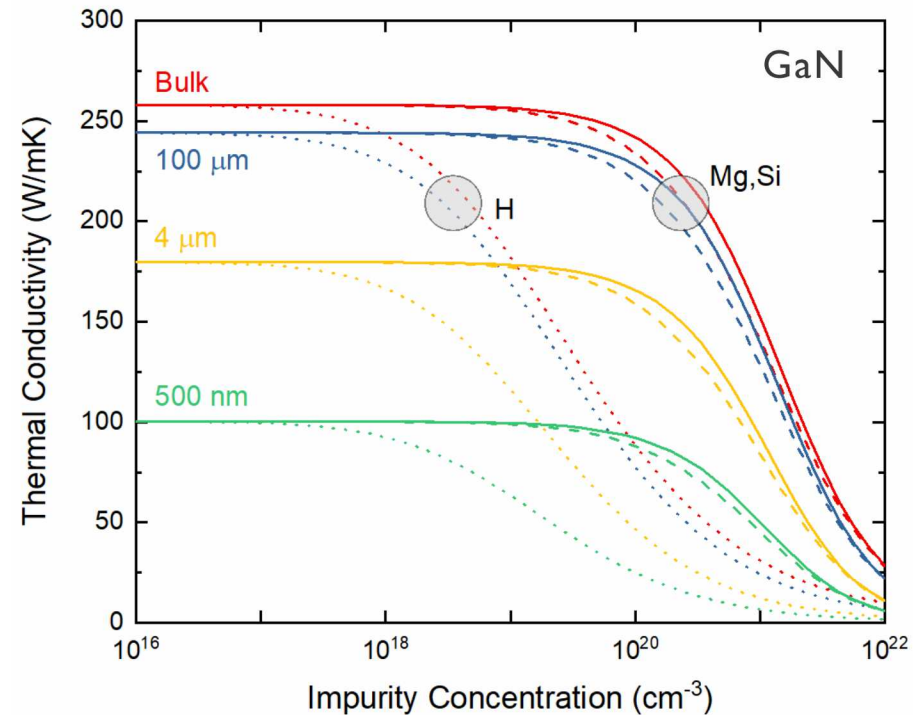
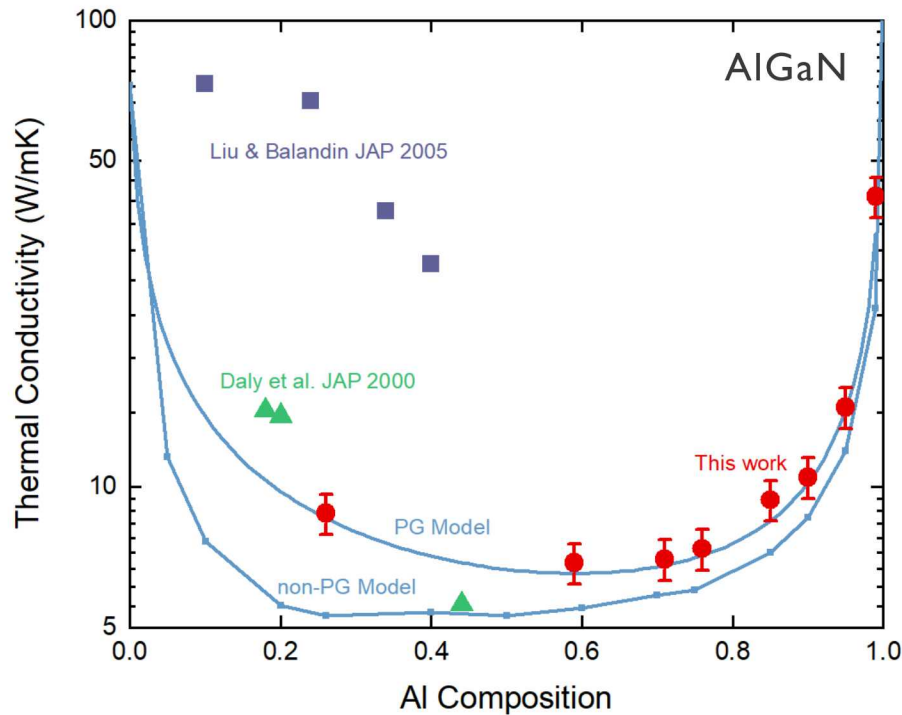
GaN conducts heat more like Si than GaN in most devices



Visualize: Why do size effects dominate?



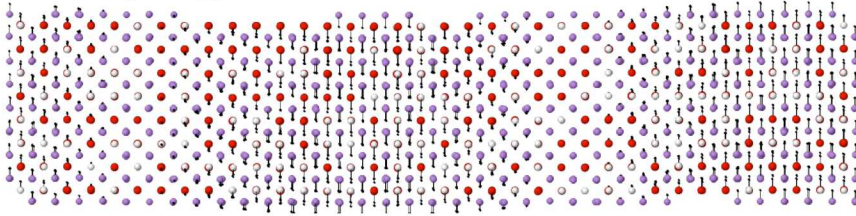
Measure: AlGaN...Impurities vs. Size Effects



Takeaway: AlGaN acts like a “normal” alloy

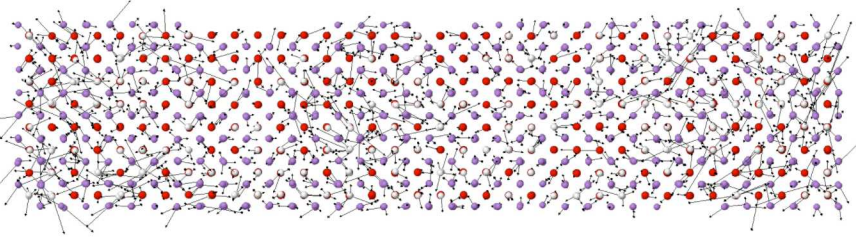
Normal alloy,
so what?

Propagons: Phonon-ish



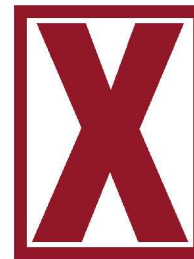
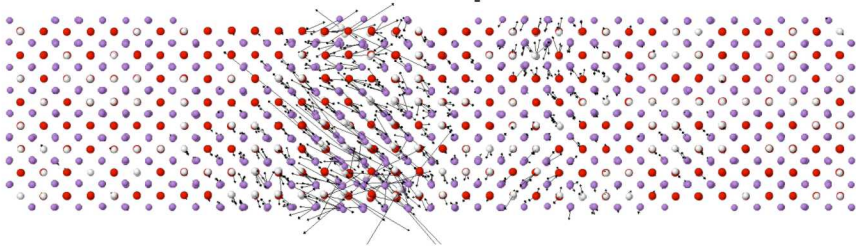
$$k = \frac{1}{6\pi^2} \sum_s \int_0^{q_{m,s}} \frac{\hbar^2 \omega^2(q)}{k_B T^2} \frac{\exp\left(\frac{\hbar \omega(q)}{k_B T}\right)}{\left[\exp\left(\frac{\hbar \omega(q)}{k_B T}\right) - 1\right]^2} v^2(q) \tau_s(q) q^2 dq$$

Diffusons: Reluctant Carriers



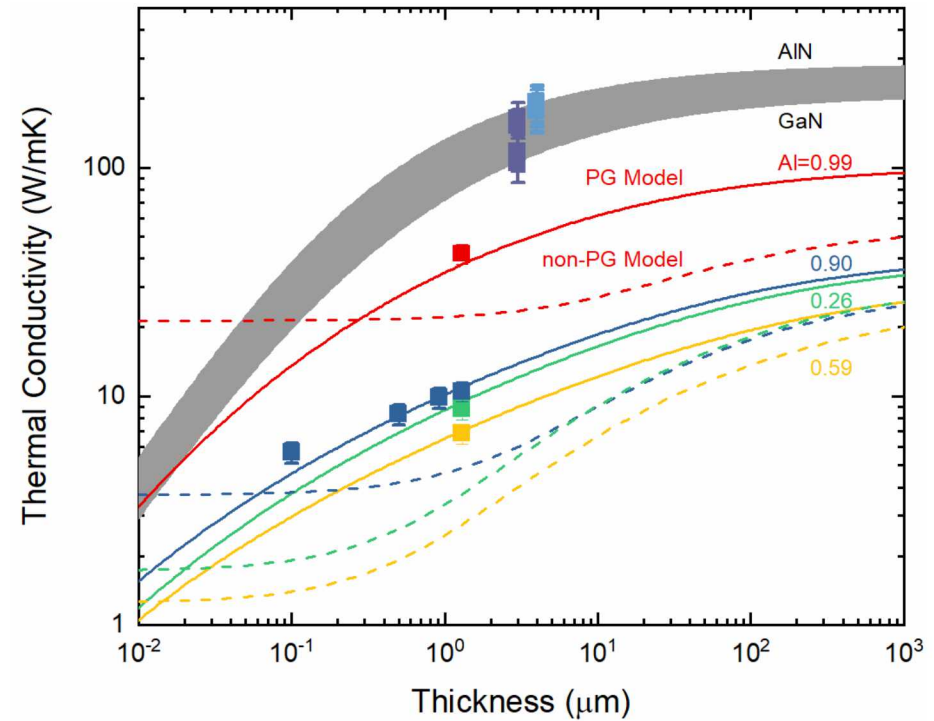
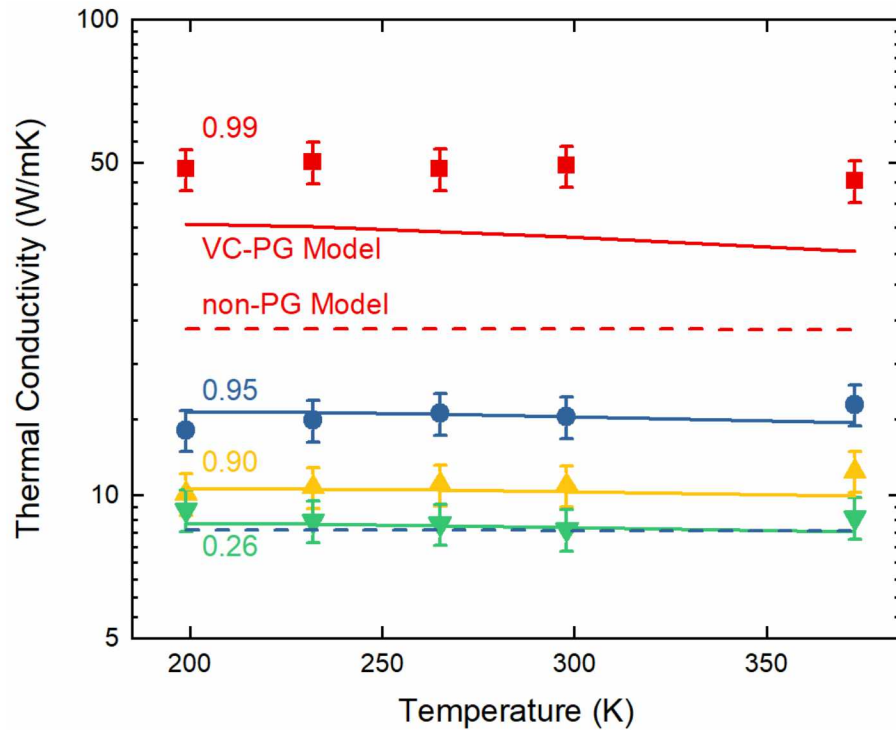
$$k_{AF} \propto \sum_i C \left(\frac{\hbar \omega}{2k_B T} \right) D_i$$

Locons: Heat Traps



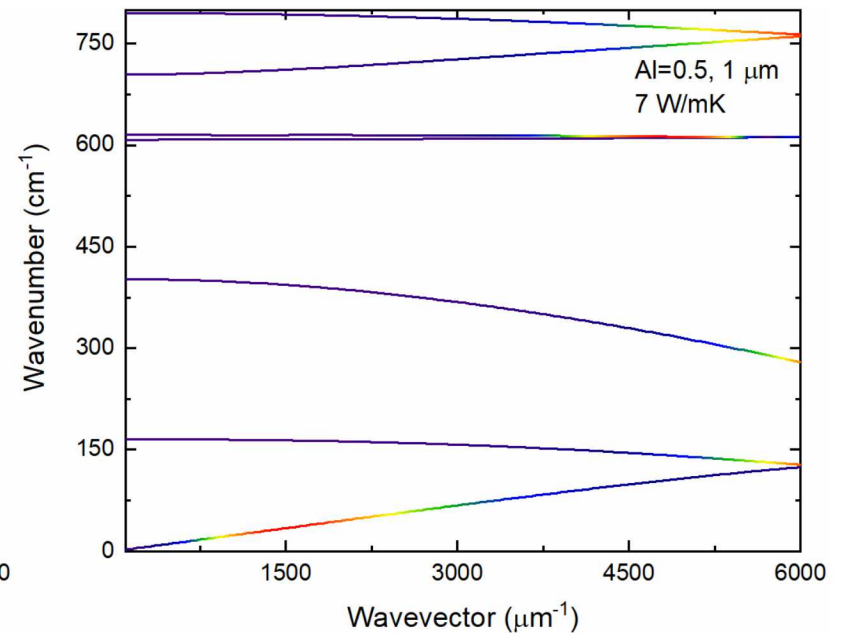
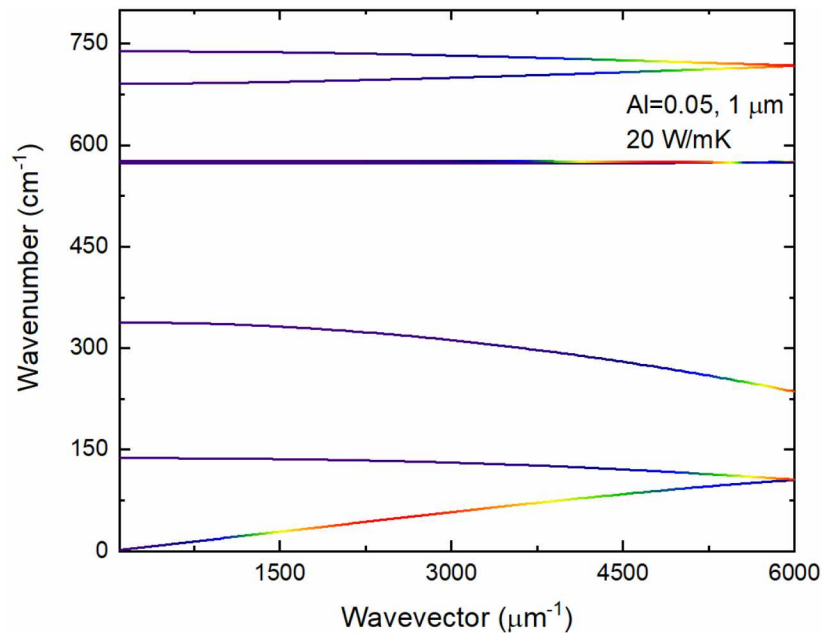
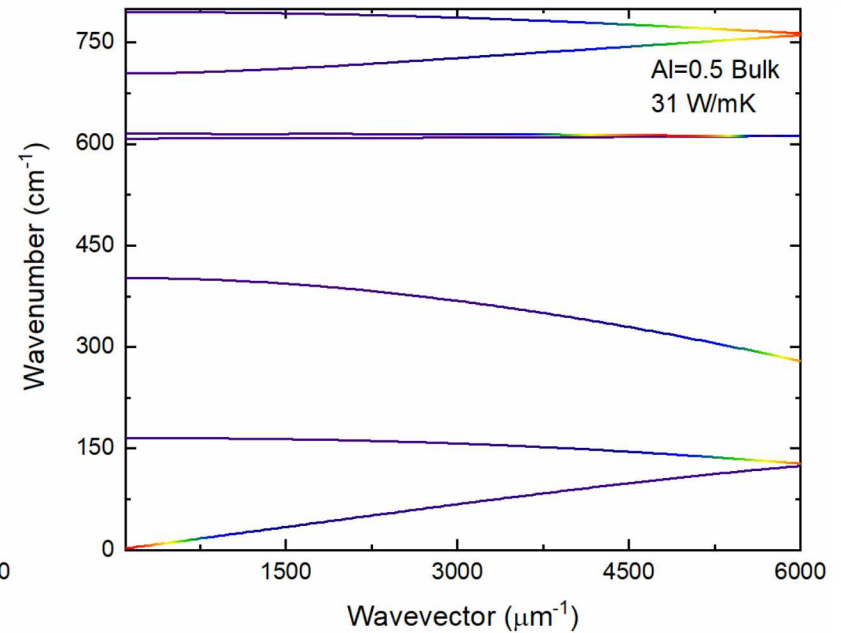
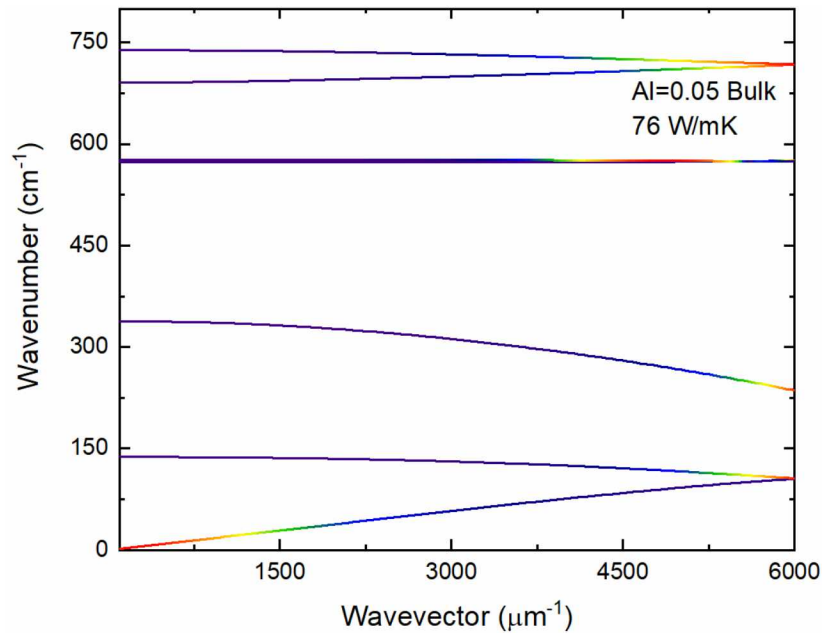
Transition between propagons & diffusons determined via modal analysis.

AlGaN: Crystal Qualities in Alloy...Size Effects too

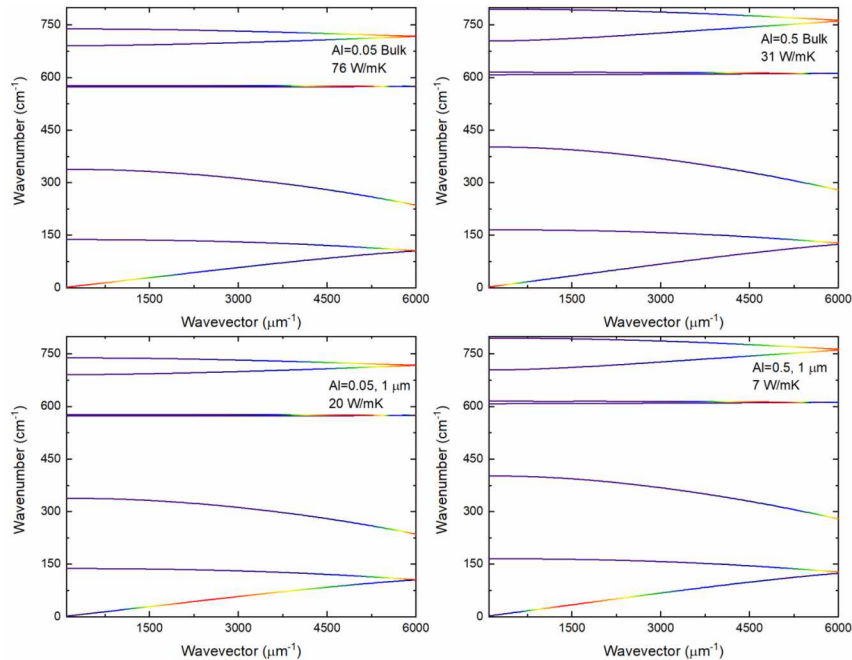


Takeaway: Size effects persist even more in alloy

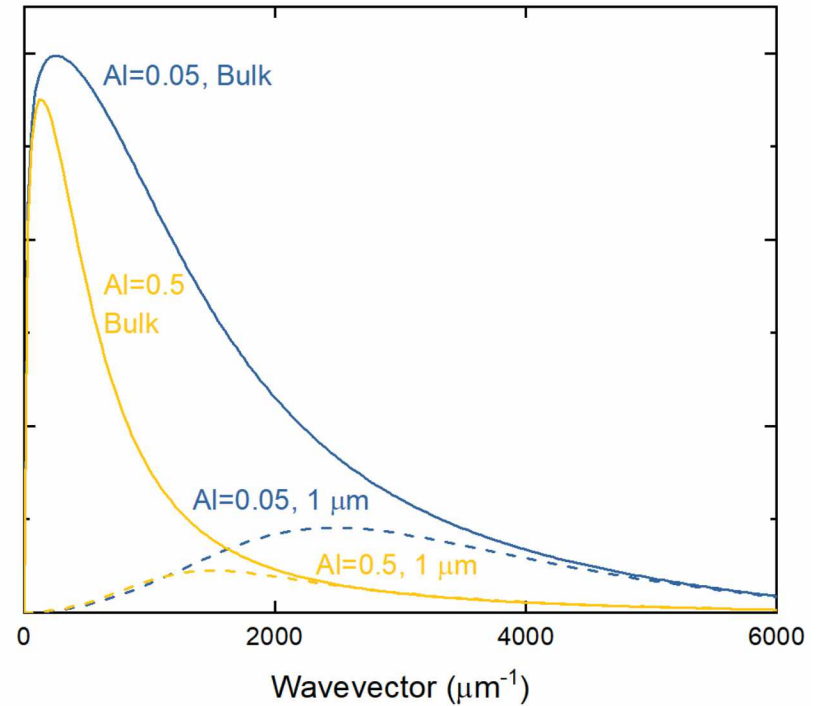
Visualize: Dominance of Acoustic Modes



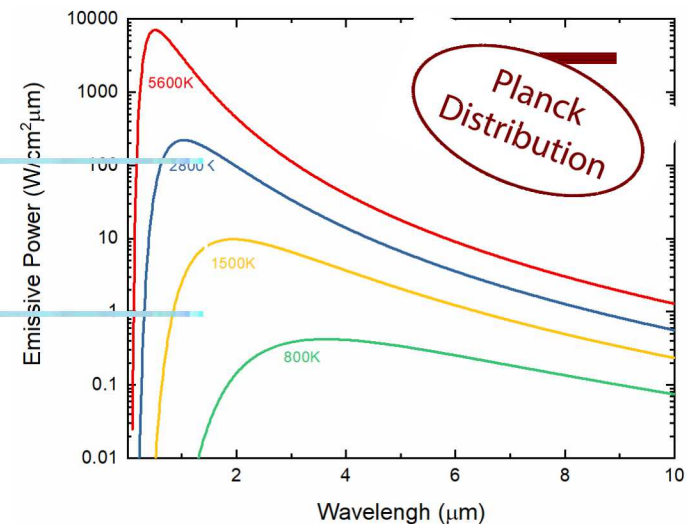
Visualize: Dominance of Acoustic Modes



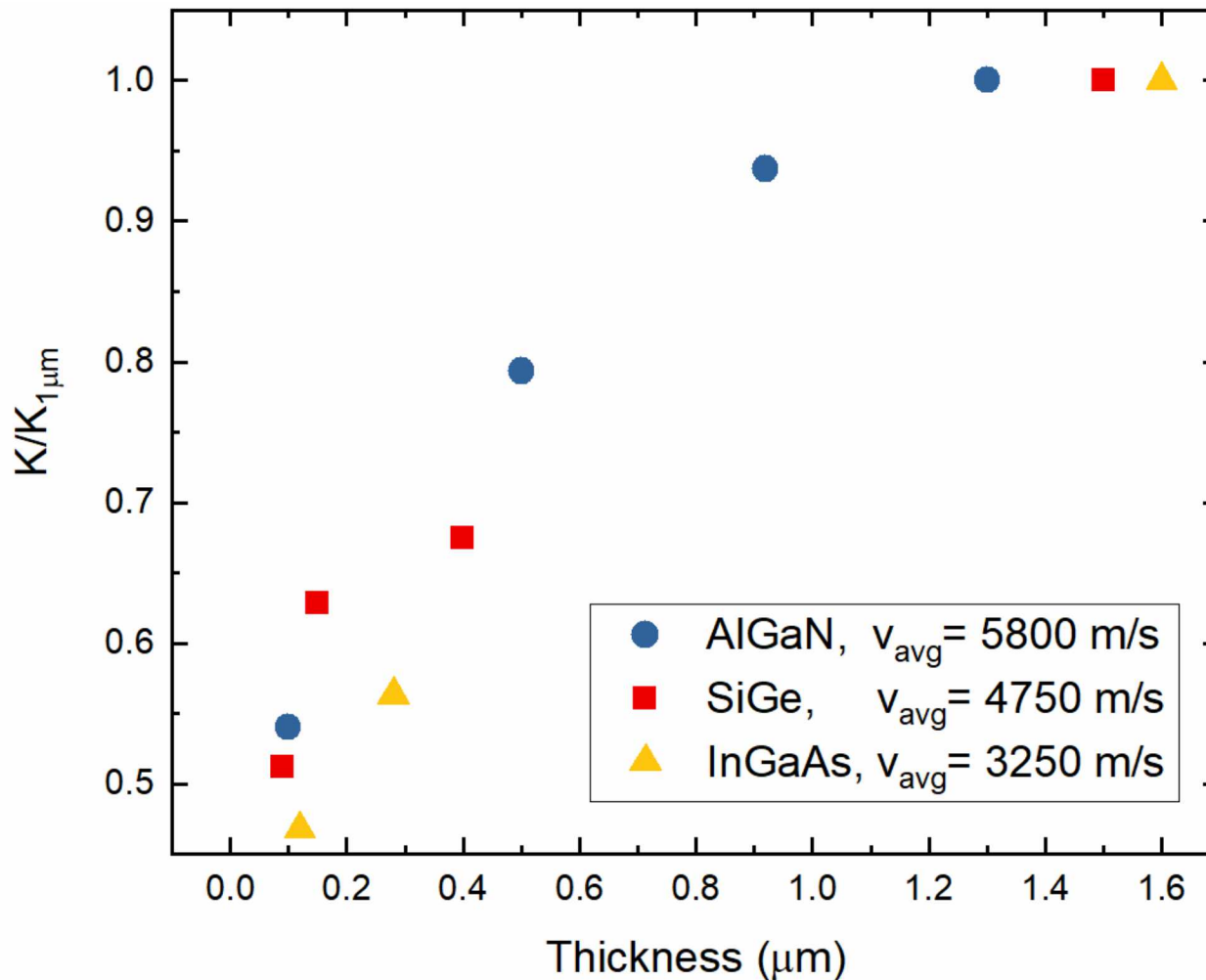
LATA Modal Therm. Cond.



Takeaway: Long-wavelength acoustic modes curtailed with size



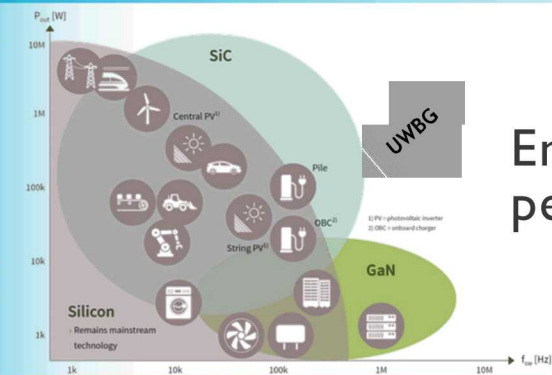
Generalize: Size Effects in Alloys



Takeaway: Size effects are similar across very different alloys

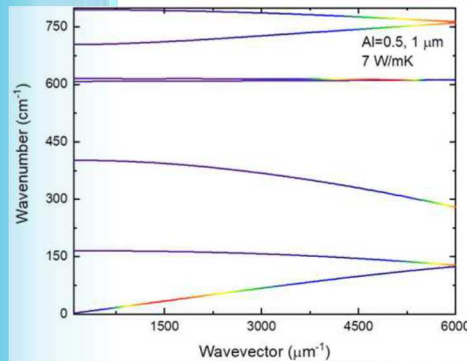
Take Home Message

Opportunity



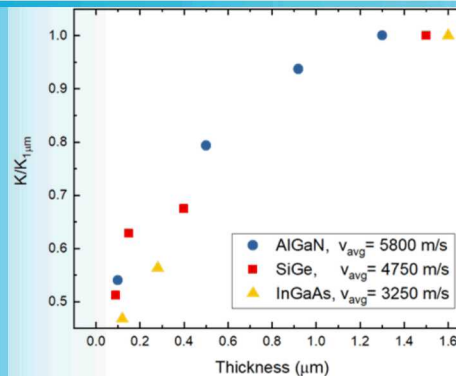
Emerging technologies provide opening to perform thermal design from “growth up.”

Insight



Size effects dominate as boundaries wreck heat carrying acoustic phonons

Model



Alloys acutely affected owing to dominance of acoustic modes.